Unit: mm

(1.0)

(1.0)

5±0

1-1-02

0.45±0.05

Base 2: Collector 3: Emitter M-A1 Package

.5+0.1

6.9±0.1

5)

(0.85)

0.55

R 0.9

3.5±0.1

.5

0.4)

R 0

0+0.

2SC4606

Silicon NPN epitaxial planar type

For low-frequency driver amplification Complementary to 2SA1762

Features

4

- \bullet High collector-emitter voltage (Base open) $V_{\mbox{\scriptsize CEO}}$
- Optimum for the driver stage of a low-frequency and 25 W to 30 W output amplifier
- M type package allowing easy automatic and manual insertion as well as stand-alone fixing to the printed circuit board

| Absolute Maximum Ratings $T_a = 25^{\circ}C$ | | | | | |
|--|------------------|-------------|------|--|--|
| Parameter | Symbol | Rating | Unit | | |
| Collector-base voltage (Emitter open) | V _{CBO} | 80 | V | | |
| Collector-emitter voltage (Base open) | V _{CEO} | 80 | V | | |
| Emitter-base voltage (Collector open) | V _{EBO} | 5 | v | | |
| Collector current | I _C | 0.5 | A | | |
| Peak collector current | I _{CP} | 1 | A | | |
| Collector power dissipation * | P _C | 1 | W | | |
| Junction temperature | Tj | 150 | °C | | |
| Storage temperature | T _{stg} | -55 to +150 | °C | | |

Electrical Characteristics $T_a = 25^{\circ}C \pm 3^{\circ}C$

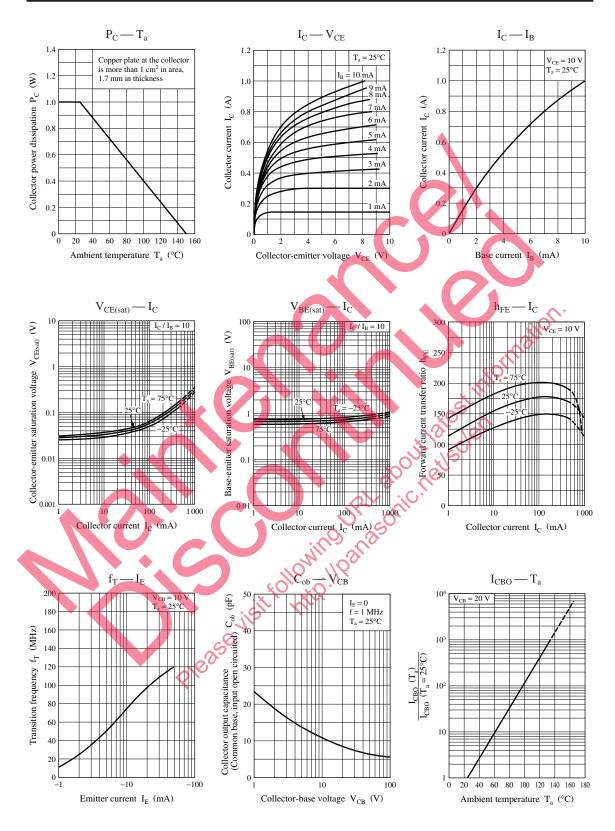
| Collector current | Ic | 0.5 | A | •. | <u> </u> | | I Fackage |
|--|----------------------|-----------------------------|---|-----|----------|-----|-----------|
| Peak collector current | I _{CP} | 1 | A | à | | | |
| Collector power dissipation * | P _C | 1 | W | XO | 0 | | |
| Junction temperature | Tj | 150 | °C | | S. | | |
| Collector current I_C 0.3 A' Peak collector current I_{CP} 1 A' Collector power dissipation * P_C 1 W' Junction temperature T_j 150 $^{\circ}C$ Storage temperature T_{stg} -55 to $+150$ $^{\circ}C$ Note) *: Copper plate at the collector is more than 1 cm ² in area, 1.7 mm in thickness $T_s = 25^{\circ}C \pm 3^{\circ}C$ | | | | | | | |
| Note) *: Copper plate at the collector is more than 1 cm ² in area, 1.7 mm | | | | | | | |
| in thickness | | | | | | | |
| Electrical Characteristics $T_a = 25^{\circ}C \pm 3^{\circ}C$ | | | | | | | |
| Parameter | Symbol | | Conditions | Min | Тур | Max | Unit |
| Collector-base voltage (Emitter open) | V _{СВО} | $I_{C} = 10 \mu$ | $J_{\rm E} = 0$ | 80 | | | V |
| Collector-emitter voltage (Base open) | V _{CEO} | $I_{\rm C} = 100 \ \mu$ | A, $I_B = 0$ | 80 | | | V |
| Emitter-base voltage (Collector open) | V _{EBO} | $J_E = 10 \ \mu \Lambda$ | 1 = 0 | 5 | | | V |
| Collector-base cutoff current (Emitter open) | I _{CBO} | $V_{\rm CB} = 20$ | $V, I_{E} = 0$ | | | 0.1 | μΑ |
| Forward current transfer ratio *1 | h _{FE1} *2 | $V_{CE} = 10$ V | V, I _C = 150 mA | 130 | | 330 | — |
| | h _{FE2} | $V_{CE} = 5 V$ | , I _C = 500 mA | 50 | 100 | | — |
| Collector-emitter saturation voltage | V _{CE(sat)} | $I_{\rm C} = 300 \text{ m}$ | nA, $I_B = 30 \text{ mA}$ | | | 0.4 | V |
| Base-emitter saturation voltage | V _{BE(sat)} | $I_{\rm C} = 300 \text{ m}$ | nA, $I_B = 30 \text{ mA}$ | | | 1.2 | V |
| Transition frequency | f _T | $V_{CB} = 10^{-1}$ | V, $I_E = -50 \text{ mA}$, $f = 200 \text{ MHz}$ | | 120 | | MHz |
| Collector output capacitance (Common base, input open circuited) | C _{ob} | V _{CB} = 10 V | V, $I_E = 0$, $f = 1$ MHz | | 11 | 20 | pF |

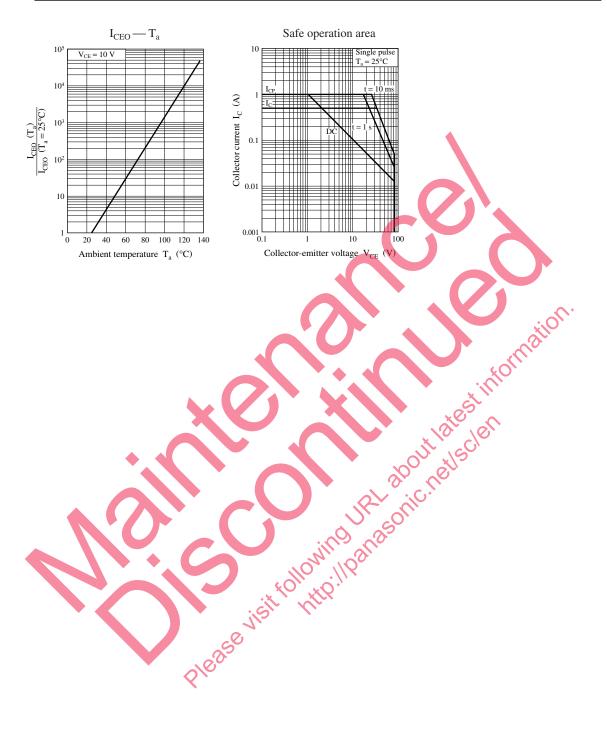
Note) 1. Measuring methods are based on JAPANESE INDUSTRIAL STANDARD JIS C 7030 measuring methods for transistors.

2. *1: Pulse measurement D - -- 1- -- 1--: c: -

| *2: Rank classification | | | | | | |
|-------------------------|------------|------------|--|--|--|--|
| Rank | R | S | | | | |
| h _{FE1} | 130 to 220 | 185 to 330 | | | | |

Note) The part number in the parenthesis shows conventional part number.





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